

SD12 300 W, 12V Plasetic Encapsulate ESD Protection Diodes

RoHS Compliant Product A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

The SD12 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

APPLICATIONS

- Stand-off voltage: 12V
- Low leakage
- Response time is typically < 1 ns
- ESD rating of class 3 (>16kV) per human body model
- IEC61000-4-2 level 4 ESD protection
- These are Pb-Free devices

DEVICE MARKING: ZC, 6U

ABSOLUTE RATINGS (T_A = 25°C)

RATING		SYMBOL	VALUE	UNIT
IEC 61000-4-2 (ESD)	Air		±15	кv
	Contact		±8.0	κν
ESD voltage	per human body model		30	KV
Total power dissipation on FR-5 Board (Note 1)		PD	200	mW
Thermal Resistance Junction-to-Ambient		R _{0JA}	625	°C / W
Junction and Storage Temperature Range		T _J , T _{STG}	-55 ~ +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)		TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the recommended. Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0 x 0.75 x 0.62 in.

ELECTRICAL CHARACTERISTICS

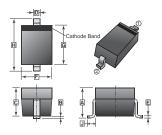
(Ratings at 25°C ambient temperature unless otherwise specified. $V_F = 0.9V$ max at $I_F = 10$ mA for all types)

PARAMETER	SYMBOL	RATING 12	UNIT V	
Working Peak Reverse Voltage (Max.)	V _{RWM}			
Maximum Reverse Leakage Current @ V _{RWM} (Max.)		I _R	1.0	μA
	Max.	N/	15.75	V
Breakdown Voltage @ I _T	Min.	V _{BR}	13.3	V
Test Current		IT	1.0	mA
Clamping Voltage @ IPP=5A		Vc	22	V
Maximum Reverse Peak Pulse Current (Max.) *		IPP	12	А
Clamping Voltage @ IPP (Max.) *		Vc	33	V
Peak Power Dissipation *		Р _{РК}	300	W
Max. Capacitance @ V _R =0 and f =1MHz (Typ.)		С	150	pF

+Surge current waveform per Figure 1.

2. V_{BR} is measured with a pulse test current I_T at an ambient temperature of $25^\circ C$

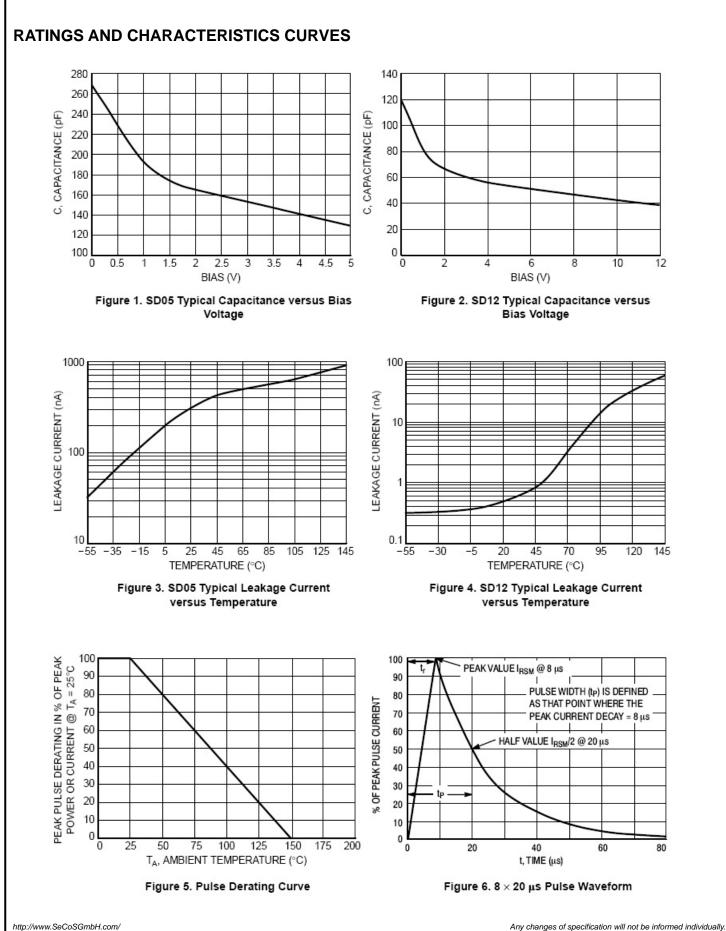
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REF.	Millimeter		REF.	Millimeter	
	Min.	Max.	KEF.	Min.	Max.
А	1.05 REF.		Е	0.080	0.180
В	0.20 REF.		F	1.15	1.45
С	0.80	1.00	G	1.60	1.80
D	0.25	0.40	Н	2.30	2.70



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nttp://www.SeCoSGmbH.con



RATINGS AND CHARACTERISTICS CURVES

